

(19) World Intellectual Property  
Organization  
International Bureau



(43) International Publication Date  
22 September 2005 (22.09.2005)

PCT

(10) International Publication Number  
**WO 2005/088743 A1**

(51) International Patent Classification<sup>7</sup>: **H01L 33/00**

(21) International Application Number:  
PCT/SG2005/000061

(22) International Filing Date: 1 March 2005 (01.03.2005)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:  
200401424-7 15 March 2004 (15.03.2004) SG

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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

**Declaration under Rule 4.17:**

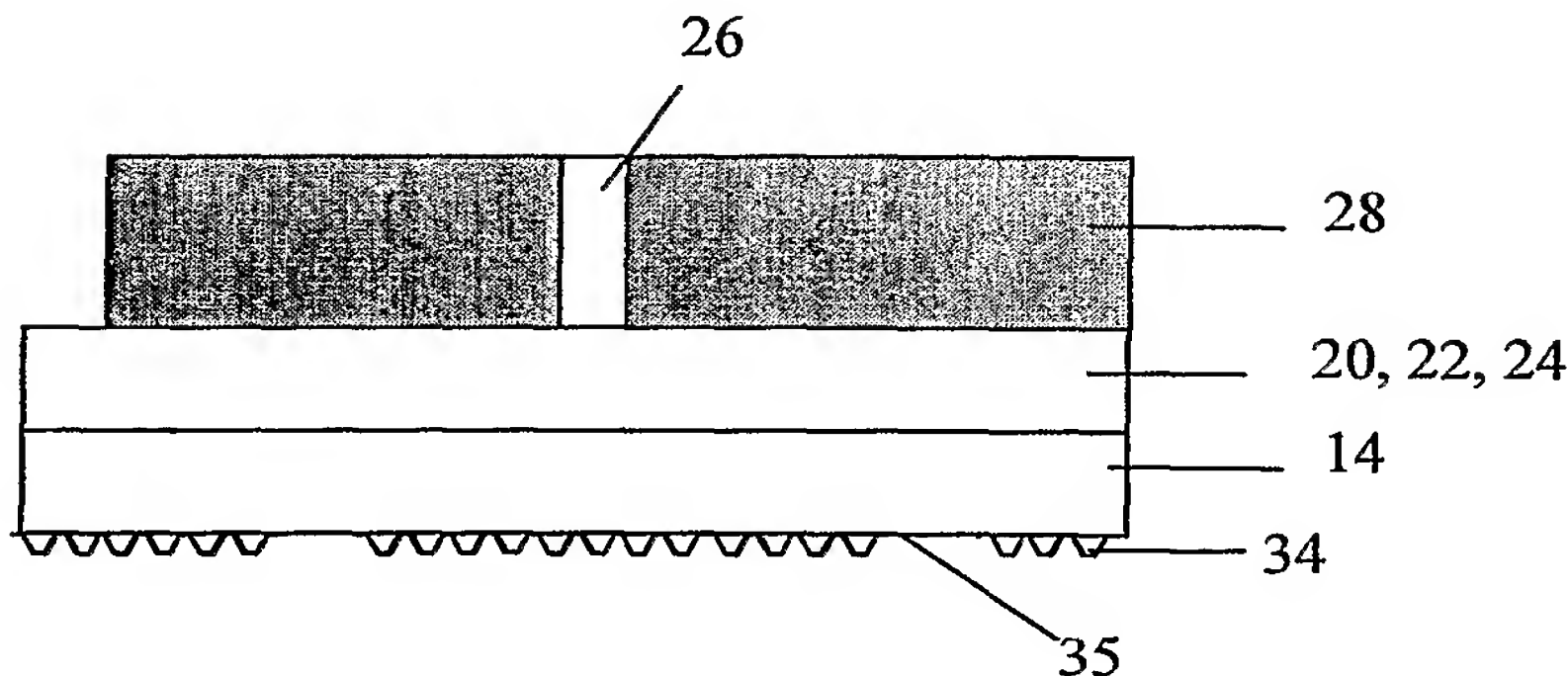
— of inventorship (Rule 4.17(iv)) for US only

**Published:**

— with international search report

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: FABRICATION OF SEMICONDUCTOR DEVICES



(57) Abstract: A method for fabrication of a semiconductor device, the semiconductor device having a plurality of epitaxial layers on a substrate. The plurality of epitaxial layers include an active region in which light is able to be generated. The method comprises applying at least one first ohmic contact layer to a front surface of the epitaxial layer, the first ohmic contact layer also acting as a reflector. The substrate is then removed from a rear surface of the

epitaxial layers. The rear surface is then textured.